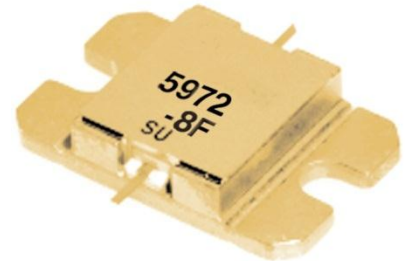


FEATURES

- High Output Power: $P_{1dB} = 39.0\text{dBm}$ (Typ.)
- High Gain: $G_{1dB} = 8.5\text{dB}$ (Typ.)
- High PAE: $\eta_{add} = 31\%$ (Typ.)
- Low $IM_3 = -45\text{dBc}@P_o = 28.0\text{dBm}$
- Broad Band: 5.9 to 7.2GHz
- Impedance Matched $Z_{in}/Z_{out} = 50\text{ohm}$
- Hermetically Sealed Package



DESCRIPTION

The FLM5972-8F is a power GaAs FET that is internally matched for standard communication bands to provide optimum power and gain in a 50 ohm system.

SEDI's stringent Quality Assurance Program assures the highest reliability and consistent performance.

ABSOLUTE MAXIMUM RATING (Case Temperature $T_c=25\text{deg.C}$)

Item	Symbol	Condition	Rating	Unit
Drain-Source Voltage	V_{DS}		15	V
Gate-Source Voltage	V_{GS}		-5	V
Total Power Dissipation	P_T	$T_c = 25\text{deg.C}$	42.8	W
Storage Temperature	T_{stg}		-65 to +175	deg.C
Channel Temperature	T_{ch}		175	deg.C

SEDI recommends the following conditions for the reliable operation of GaAs FETs:

1. The drain-source operating voltage (V_{DS}) should not exceed 10 volts.
2. The forward and reverse gate currents should not exceed 32.0 and -4.4 mA respectively with gate resistance of 100ohm.

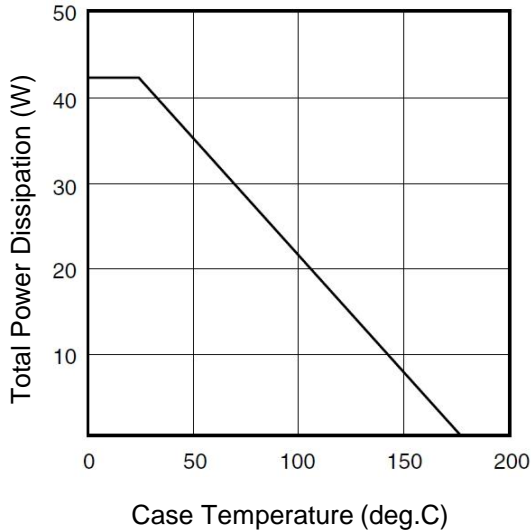
ELECTRICAL CHARACTERISTICS (Case Temperature $T_c=25\text{deg.C}$)

Item	Symbol	Test Conditions	Limit			Unit
			Min.	Typ.	Max.	
Saturated Drain Current	I_{DSS}	$V_{DS}=5V, V_{GS}=0V$	-	3400	5200	mA
Transconductance	g_m	$V_{DS}=5V, I_{DS}=2200\text{mA}$	-	3400	-	mS
Pinch-off Voltage	V_p	$V_{DS}=5V, I_{DS}=170\text{mA}$	-0.5	-1.5	-3.0	V
Gate Source Breakdown Voltage	V_{GSO}	$I_{GS}=-170\mu\text{A}$	-5.0	-	-	V
Output Power at 1dB G.C.P.	P_{1dB}	$V_{DS}=10V,$ $I_{DS}=0.65 I_{DSS}$ (Typ.), $f=5.9$ to 7.2 GHz, $Z_S=Z_L=50\text{ohm}$	38.0	39.0	-	dBm
Power Gain at 1dB G.C.P.	G_{1dB}		7.5	8.5	-	dB
Drain Current	I_{dsr}		-	2200	2600	mA
Power-added Efficiency	η_{add}		-	31	-	%
Gain Flatness	ΔG		-	-	1.2	dB
3rd Order Intermodulation Distortion	IM_3	$f = 7.2$ GHz, $\Delta f = 10$ MHz 2-Tone Test $P_{out} = 28.0\text{dBm}$ S.C.L.	-42	-45	-	dBc
Thermal Resistance	R_{th}	Channel to Case	-	3.0	3.5	deg.C/W
Channel Temperature Rise	ΔT_{ch}	$10V \times I_{dsr} \times R_{th}$	-	-	80	deg.C

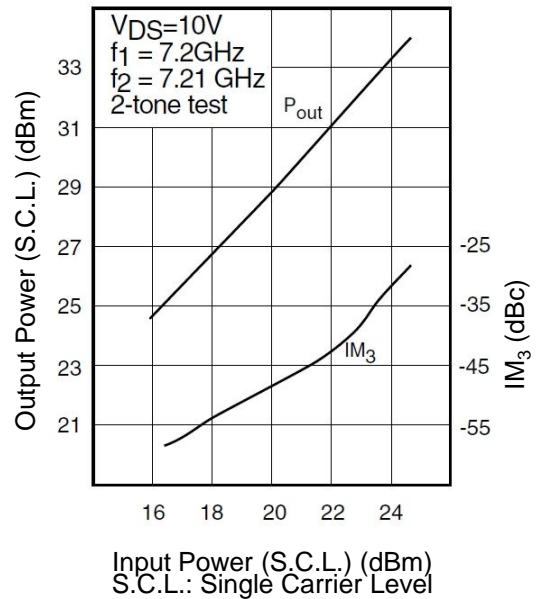
G.C.P.: Gain Compression Point, S.C.L.: Single Carrier Level

CASE STYLE	IB	
ESD	Class 3A	4000V to 8000V
Note : Based on JEDEC JESD22-A114 (C=100pF, R=1.5kohm)		
RoHS Compliance	Yes	

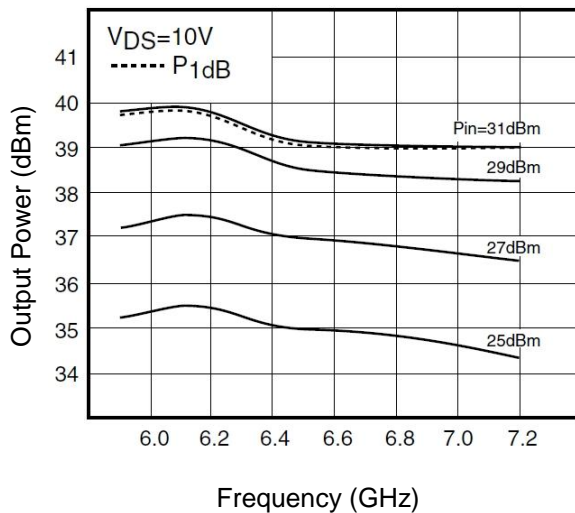
POWER DERATING CURVE



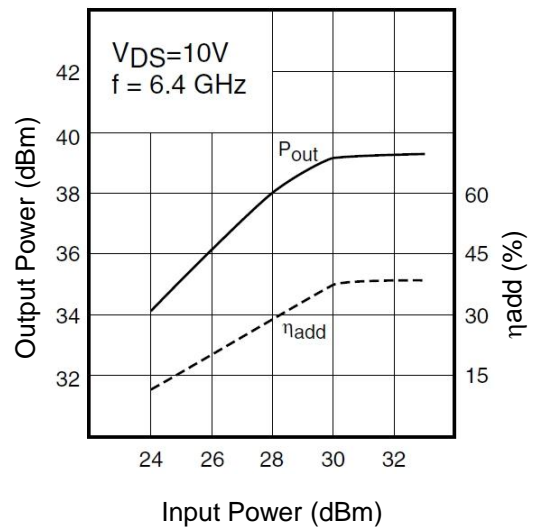
OUTPUT POWER & IM₃ vs. INPUT POWER

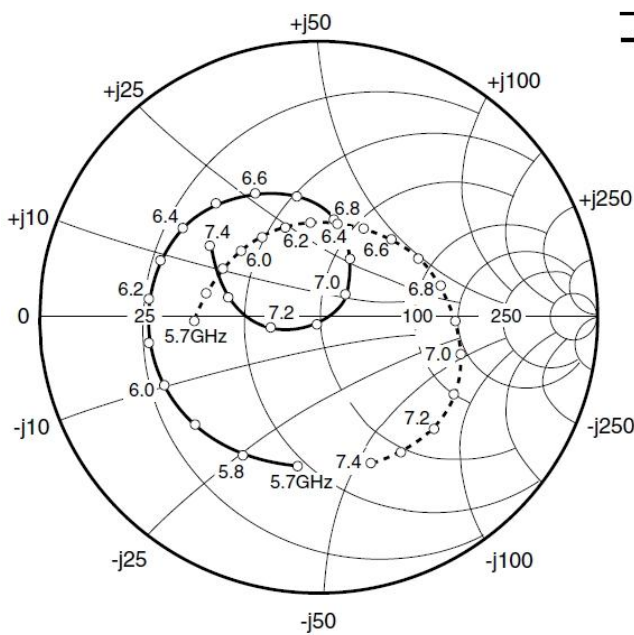


OUTPUT POWER vs. FREQUENCY

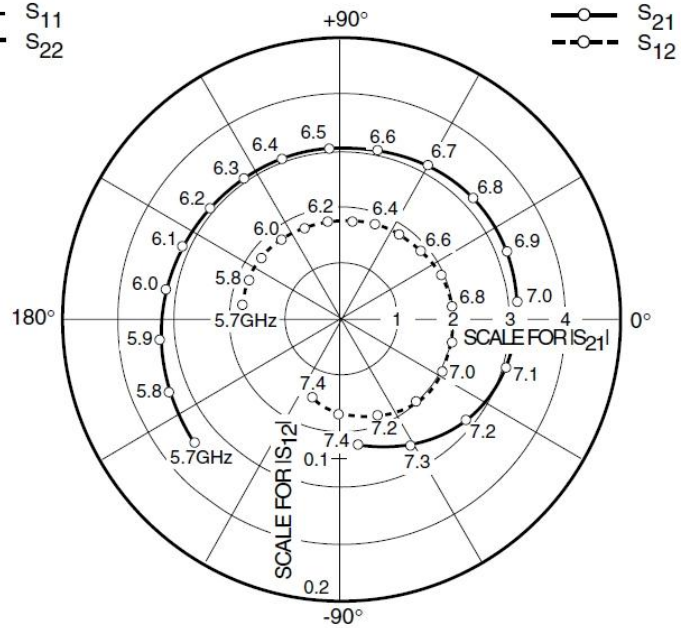


OUTPUT POWER vs. INPUT POWER





—○— S₁₁
- -○- - S₂₂



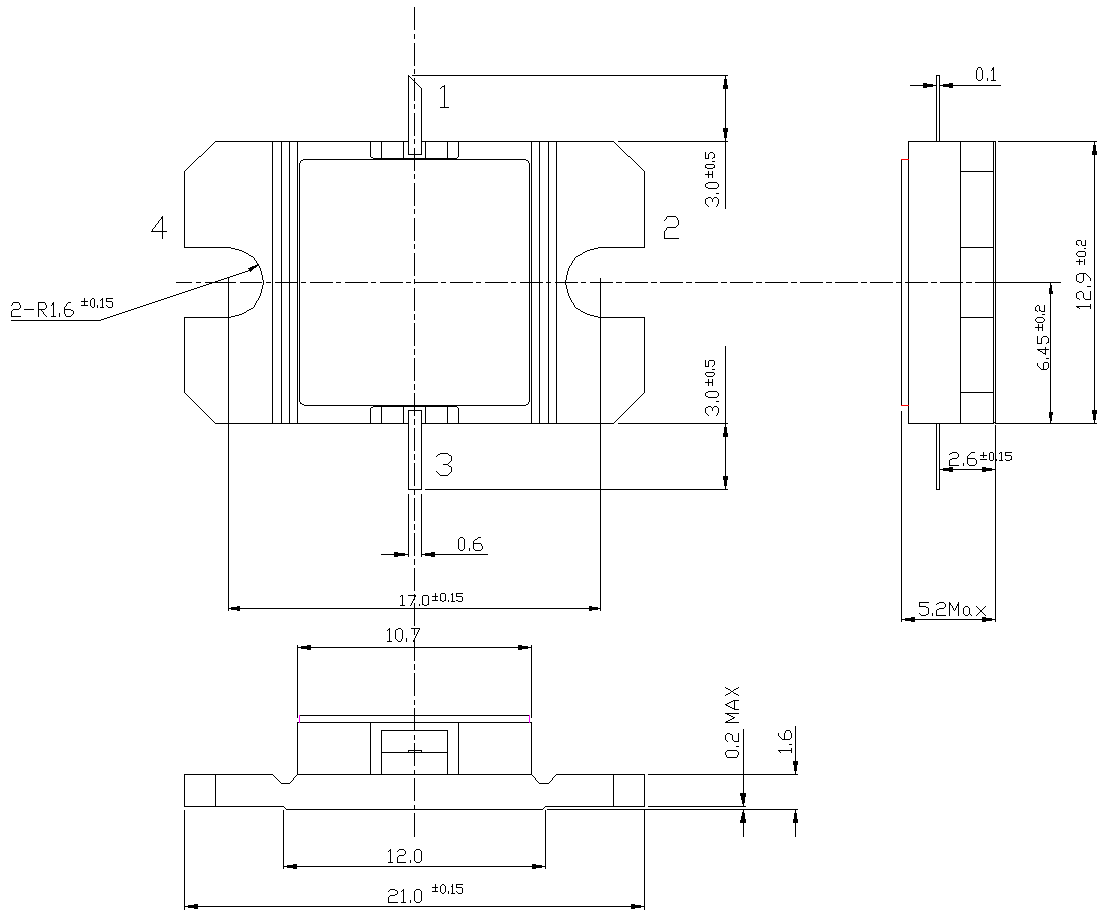
—○— S₂₁
- -○- - S₁₂

S-PARAMETERS

V_{DS} = 10V, I_{DS} = 2200mA

FREQUENCY (MHz)	S11		S21		S12		S22	
	MAG	ANG	MAG	ANG	MAG	ANG	MAG	ANG
5700	0.543	-98.0	3.435	-140.7	0.071	172.5	0.446	-178.5
5800	0.566	-119.0	3.366	-157.0	0.071	156.9	0.416	167.7
5900	0.586	-138.3	3.291	-173.2	0.071	142.6	0.388	153.6
6000	0.603	-155.7	3.209	171.2	0.070	127.4	0.368	139.8
6100	0.613	-171.5	3.133	155.8	0.069	112.0	0.353	125.4
6200	0.616	174.1	3.078	140.6	0.070	98.4	0.344	110.5
6300	0.607	160.0	3.047	125.5	0.070	83.7	0.342	95.4
6400	0.583	146.1	3.039	110.3	0.071	69.9	0.349	79.5
6500	0.551	131.7	3.049	94.1	0.073	55.3	0.362	63.5
6600	0.503	116.7	3.088	78.0	0.076	39.9	0.386	46.9
6700	0.438	100.4	3.130	60.7	0.078	23.5	0.418	30.7
6800	0.351	82.5	3.165	42.3	0.079	7.3	0.455	14.4
6900	0.245	62.3	3.182	22.7	0.082	-11.7	0.496	-1.7
7000	0.130	39.9	3.150	5.5	0.082	-27.5	0.531	-14.2
7100	0.029	-98.9	3.037	-16.5	0.080	-48.4	0.561	-30.1
7200	0.175	-166.2	2.839	-38.7	0.074	-68.9	0.576	-44.8
7300	0.328	168.6	2.562	-60.8	0.069	-90.0	0.577	-58.2
7400	0.469	146.1	2.243	-82.4	0.059	-110.2	0.561	-70.3

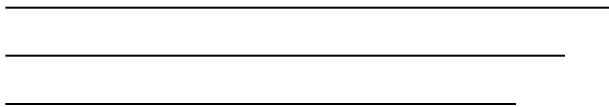
■ Package Outline
Case Style : IB



Pin Assignment

- 1 : Gate
- 2 : Source
- 3 : Drain
- 4 : Source

Unit : mm



FLM5972-8F

C-Band Internally Matched FET

For further information please contact:

<http://global-sei.com/Electro-optic/about/office.html>

CAUTION

This product contains **gallium arsenide (GaAs)** which can be hazardous to the human body and the environment. For safety, observe the following procedures:

- Do not put these products into the mouth.
- Do not alter the form of this product into a gas, powder, or liquid through burning, crushing, or chemical processing as these by-products are dangerous to the human body if inhaled, ingested, or swallowed.
- Observe government laws and company regulations when discarding this product. This product must be discarded in accordance with methods specified by applicable hazardous waste procedures.